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(54) **THIN FILM TRANSISTOR SUBSTRATE AND METHOD OF MANUFACTURING THE SAME AND DISPLAY APPARATUS COMPRISING THE SAME**

(52) **U.S. Cl.**

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ABSTRACT

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Disclosed is a thin film transistor substrate including a first thin film transistor having a first gate electrode, a first active layer, a first source electrode, and a first drain electrode, and a second thin film transistor having a second gate electrode, a second active layer with a pattern different from a pattern of the first active layer, a second source electrode, and a second drain electrode. The first active layer includes a first lower active layer overlapping the first gate electrode and a first upper active layer disposed on the first lower active layer and not overlapping the first gate electrode. The second active layer includes a second lower active layer overlapping the second gate electrode and a second upper active layer disposed on the second lower active layer and overlapping the second gate electrode. A display apparatus including the same thin film transistor substrate is also disclosed.

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